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Tomohiro Kawase et al.

Filing Date

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U.S. Patent Documents							
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	AA						
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	AL							
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Other Documents (include Author, Title, Date, and Place of Publication)						
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107	D1	Hein, "Growth of Semiinsulating GaAs Crystals by Vertical Gradient Freeze Technique," Crystal Research Technology v. 30, No. 7, pp. 897-909 (1995)				
	D1A	Hein et al, "Die Kristallisation and Schmelzen aus metallurgischer Prozess," Metall, v. 47, No. 10, pp. 924-928 (Oct. 1993)				
	D2	Flade, "Entwicklung gross flächriger GaAs-Substrate," Freiberger Elektronikwerkstoffe GmbH (Hannover, Germany, February 19, 1996) (?)				

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